

<b>FORM 1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b> (Use several sheets if necessary)	Docket Number: 10873.1440US01	Application Number: 10/809,033
	Applicant: SASAKI et al.	
	Filing Date: March 25, 2004	Group Art Unit: Unknown

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

  

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
GNR D.H.GNR	2004/013385	02.2004	WO				

  

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
GNR D.H.GNR	Imade et al., "Growth of Bulk GaN Single Crystals by High-Pressure Sublimation Method", Proceedings of the 48th Symposium on Synthetic Crystals, IA06, pp 23-24, 11-4-2003 (GNR 518107).
GNR D.H.GNR	Imade et al. "Growth of Thick GaN Films with High Growth Rate Using Sublimation Method under High Pressure", Jpn. J. Appl. Phys., Vol. 43 (2004), pp. L486-L488

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PATENT TRADEMARK OFFICE

(second consideration) 5/8/07.

EXAMINER	DATE CONSIDERED 3-4-6
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.